

TECHNICAL DATA  
DATASHEET 4226, Rev-

**FAST RECOVERY  
SILICON RECTIFIER DIE**

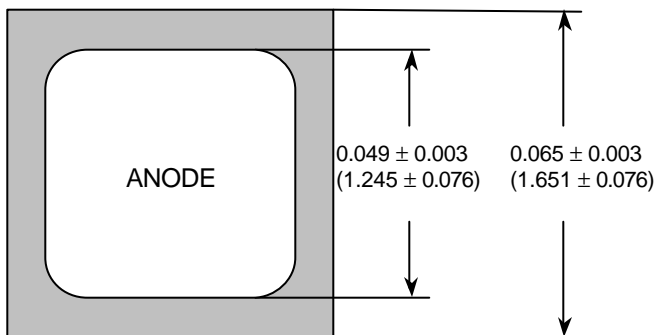
**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	400	V
Max. Average Forward Current	$I_{F(AV)}$	@ 25°C	3.0	A
Die Size	-	-	65	mil
Max. Junction Temperature	$T_J$	-	-65 to +175	°C
Max. Storage Temperature	$T_{stg}$	-	-65 to +175	°C

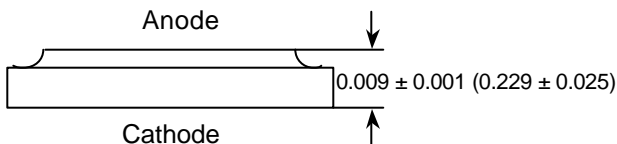
**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 9.0A, Pulse, $T_J = 25\text{ °C}$	1.5	V
		Duty cycle $\leq 2\%$ , pulse width $\leq 300\mu s$		
Max. Reverse Current	$I_{R1}$	@ $V_R = 400V$ , Pulse, $T_J = 25\text{ °C}$	2.0	$\mu A$
	$I_{R2}$	@ $V_R = 400V$ , Pulse, $T_J = 100\text{ °C}$	100	$\mu A$
Reverse Recovery Time	$t_{rr}$	$I_f = 500mA$ , $I_r = 1A$ , $I_{rm} = 250mA$	400	ns
Max. Junction Capacitance	$C_T$	$T_C = 25\text{ °C}$ , $f_{SIG} = 1MHz$ , $V_{SIG} = 50mV$ (p-p)		
		$V_R = 0V$	180	pF
		$V_R = 4V$	90	pF

**Mechanical Dimensions: In Inches / mm**



Top side metalization - Aluminum - 25 kÅ  
Bottom side metalization - Titanium 1.0 kÅ,  
Nickel 1.5 kÅ, Silver - 25 kÅ minimum  
Bottom side is cathode, top side is anode.



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